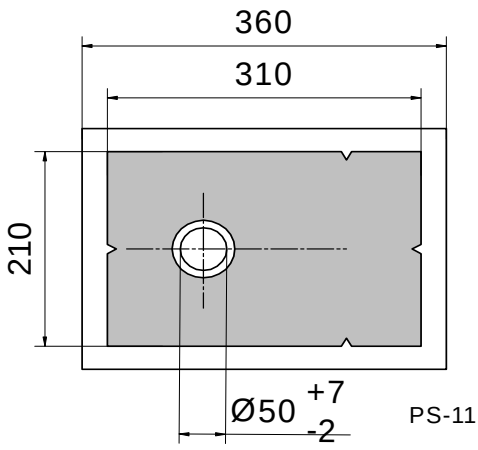


Radiation	Type	Technology	Electrodes
Infrared	Point Source	AlGaAs/GaAs	P (anode) up

	typ. dimensions (μm)	
	typ. thickness 300 (± 20) μm	
	anode gold alloy, 1.5 μm	
	cathode gold alloy, 0.5 μm	

Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			50	mA
Peak forward current	$t_p \leq 50 \mu\text{s}$, $t_p/T = 1/2$	I_{FM}			100	mA

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.4	1.8	V
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1.5		V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	5			V
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e	0.4	0.6		mW
Radiant power*	$I_F = 50 \text{ mA}$	Φ_e		1.9		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	865	875	885	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		40		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		16		ns

*Measured on bare chip on TO-18 header with EPIGAP equipment

Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-875-19-20				

Packing: Chips on adhesive film with wire-bond side on top

We reserve the right to make changes to improve technical design and may do so without further notice.
Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.